

Amendments to the Claims

Claims 1-59 (Cancelled).

60. (Currently amended) A semiconductor processing method of depositing SiO₂ on a substrate comprising:

providing a substrate within a cold-wall chemical vapor deposition reactor, the ~~chemical vapor deposition reactor being a cold wall reactor;~~

providing rf power of 600W and a temperature of about 400°C within the chemical vapor deposition reactor;

injecting liquid TEOS feeding a gaseous silicon precursor into the chemical vapor deposition reactor at 975 sccm;

feeding gaseous H₂O₂ into the chemical vapor deposition reactor; and

decomposing the TEOS to form SiO₂ and depositing the SiO₂ onto the substrate; the decomposing being conducted at a pressure of from about 10 Torr to about 80 Torr.

~~without feeding added ozone to the chemical vapor deposition reactor, utilizing the silicon precursor to directly deposit SiO₂ over a surface of the substrate to form an as-deposited layer of SiO₂, the SiO₂ being formed during the directly depositing.~~

61. (Currently amended) The semiconductor processing method of claim 60 wherein the gaseous H₂O₂ and the TEOS ~~gaseous silicon precursor~~ are fed into the chemical vapor deposition reactor independently.

62. (Currently amended) The semiconductor processing method of claim 60 wherein the gaseous H_2O_2 and the TEOS ~~gaseous silicon precursor~~ are fed into the chemical vapor deposition reactor simultaneously.

63. (Cancelled)

64. (Previously presented) The semiconductor processing method of claim 60 further comprising feeding gaseous H_2O into the chemical vapor deposition reactor.

65. (Cancelled).

66. (Currently amended) The semiconductor processing method of claim 60 wherein the surface of the substrate comprises a high aspect ratio topology and wherein the SiO_2 layer is conformally deposited over the topology.

67-70. (Cancelled)